

Features

- Center amplifying gate
- Metal case with ceramic insulator
- Low on-state and switching losses

Typical Applications

- AC controllers
- DC and AC motor control
- Controlled rectifiers

品名: FH700T**

 $I_{T(AV)}$ 700A V_{DRM}, V_{RRM} 8000V

8500V



SYMBOL	CHARACTERISTIC	TEST CONDITIONS	$T_j(^{\circ}C)$	VALUE			UNIT
				Min	Type	Max	
$I_{T(AV)}$	Mean on-state current	180° half sine wave 50Hz Double side cooled, $T_c=70^{\circ}C$	125			700	A
I_{DRM} I_{RRM}	Repetitive peak current	at V_{DRM} $t_p=10ms$ at V_{RRM} $t_p=10ms$	125			200	mA
I_{TSM}	Surge on-state current	10ms half sine wave $V_R=0.6V_{RRM}$	125			9.8	kA
I^2t	I^2t for fusing coordination					480	$A^2s \times 10^3$
V_{TO}	Threshold voltage		125			1.04	V
r_T	On-state slope resistance					1.50	$m\Omega$
V_{TM}	Peak on-state voltage	$I_{TM}=1000A$, $F=24kN$	25			2.65	V
dv/dt	Critical rate of rise of off-state voltage	$V_{DM}=0.67V_{DRM}$	125			2000	$V/\mu s$
di/dt	Critical rate of rise of on-state current	$V_{DM}=67\%V_{DRM}$ Gate pulse $t_r \leq 0.5\mu s$ $I_{GM}=2.0A$	125			100	$A/\mu s$
Q_{rr}	Recovery charge	$I_{TM}=2000A$, $t_p=4000\mu s$, $di/dt=-5A/\mu s$, $V_R=50V$	125		2500		μC
I_{GT}	Gate trigger current	$V_A=12V$, $I_A=1A$	25	40		300	mA
V_{GT}	Gate trigger voltage			0.8		3.0	V
I_H	Holding current			25		200	mA
V_{GD}	Non-trigger gate voltage	$V_{DM}=0.67V_{DRM}$	125	0.3			V
$R_{th(j-C)}$	Thermal resistance Junction to case	DC Double side cooled Clamping force 24.0kN				0.022	$^{\circ}C/W$
$R_{th(C-h)}$	Thermal resistance case to heatsink					0.004	$^{\circ}C/W$
F_m	Mounting force			19	24	26	kN
T_{stg}	Stored temperature			-40		140	$^{\circ}C$
W_t	Weight				560		g
Outline		P24					

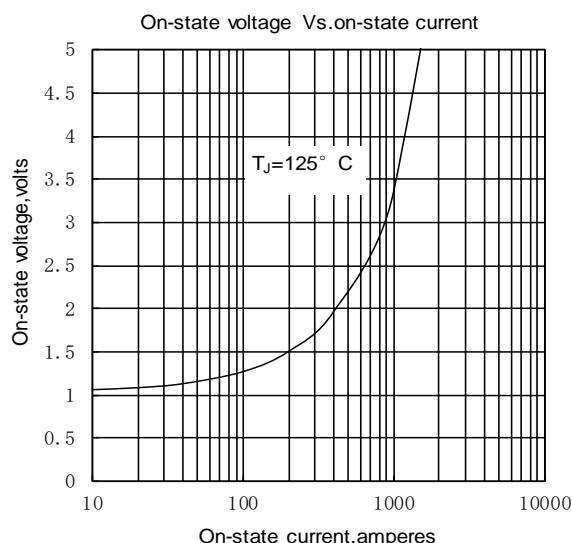


Fig.1

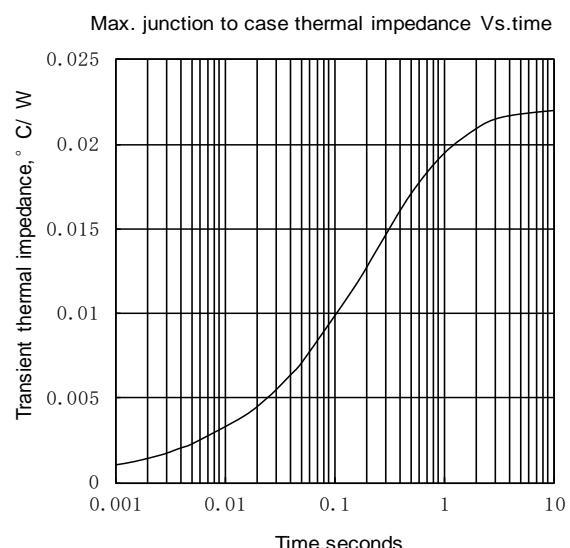


Fig.2

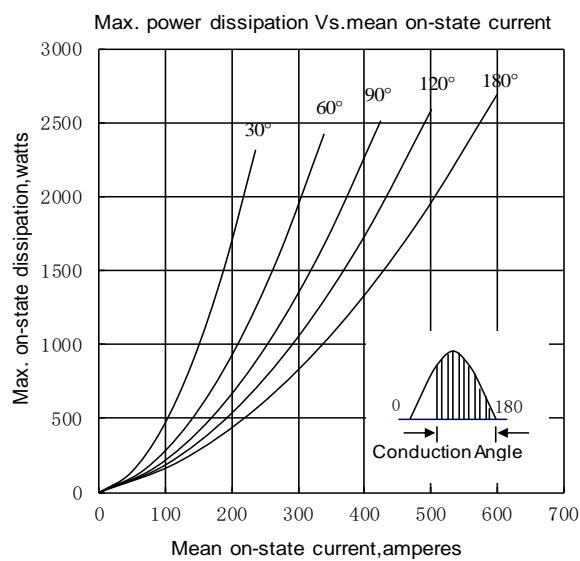


Fig.3

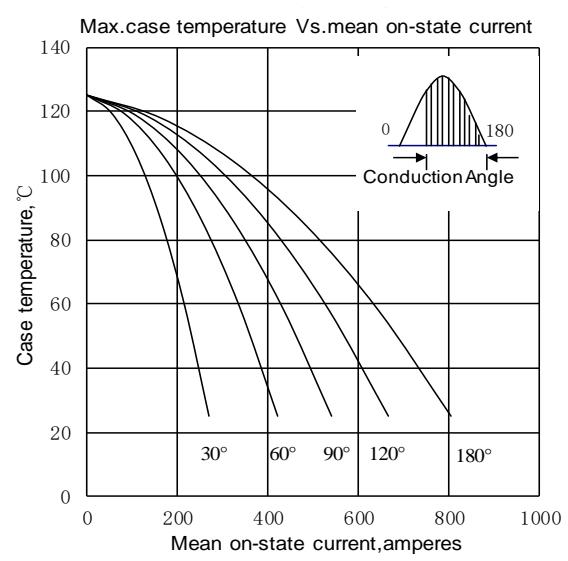


Fig.4

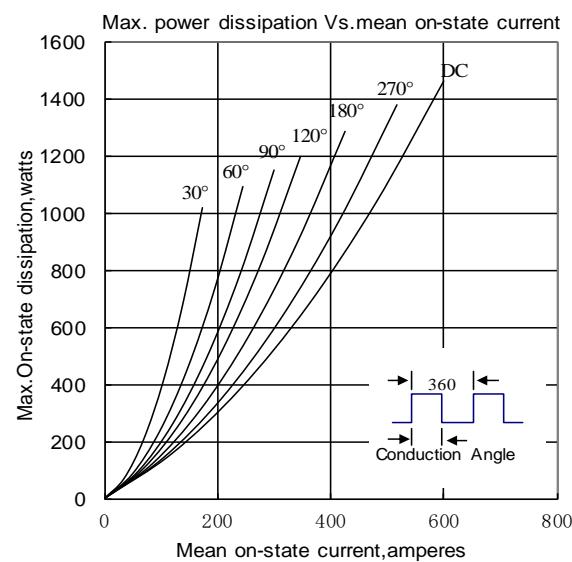


Fig.5

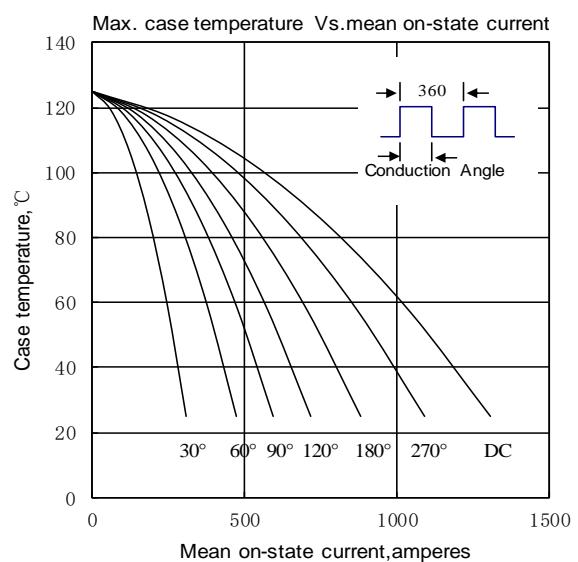


Fig.6

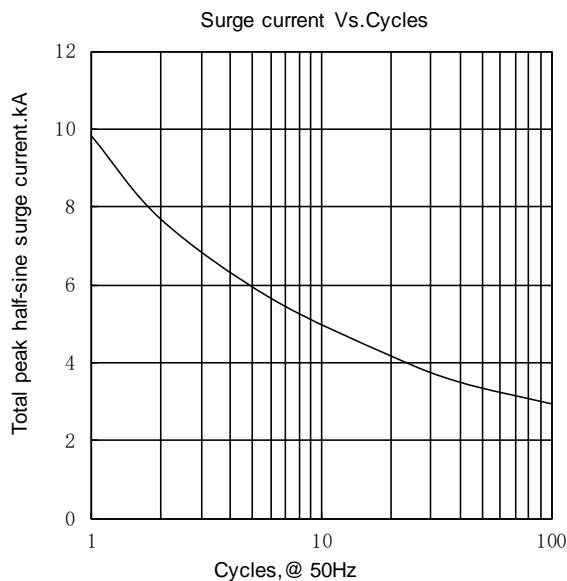


Fig.7

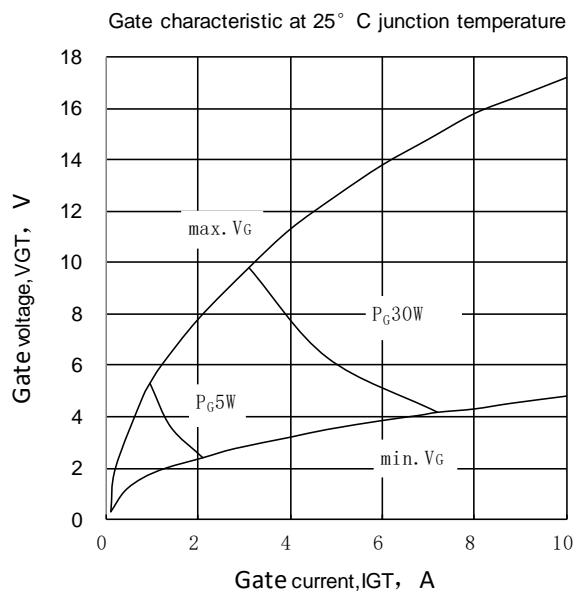


Fig.8

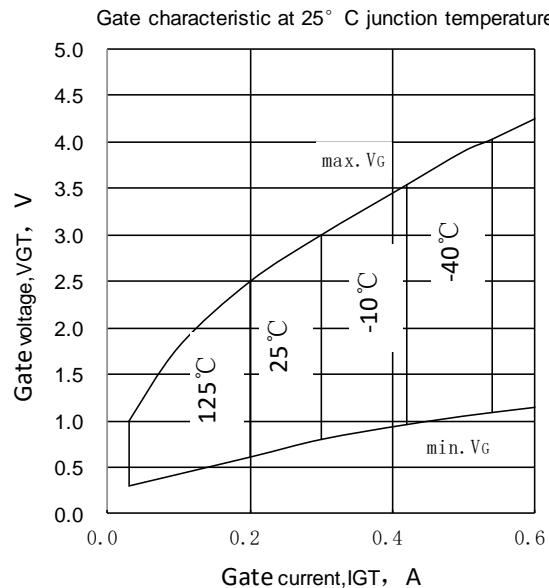
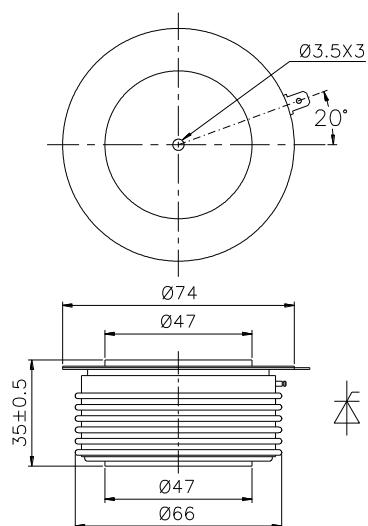


Fig.9



Nips reserves the right to change specifications without notice.